ELECTRONICS, INC.
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BLOOMFIELD, NJ 07003
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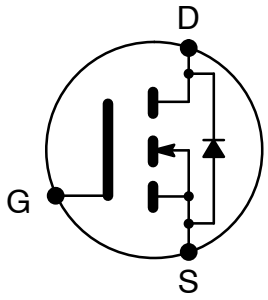
NTE2976
MOSFET
N–Channel, Enhancement Mode
High Speed Switch
TO220 Full Pack Type Package

Features:
- Low Input Capacitance
- Low Static $R_{DS(on)}$
- Fast Switching Time
- Guaranteed Avalanche Resistance



Applications:
- Switching Power Supply of AC 240V Input
- High Voltage Power Supply
- Inverter

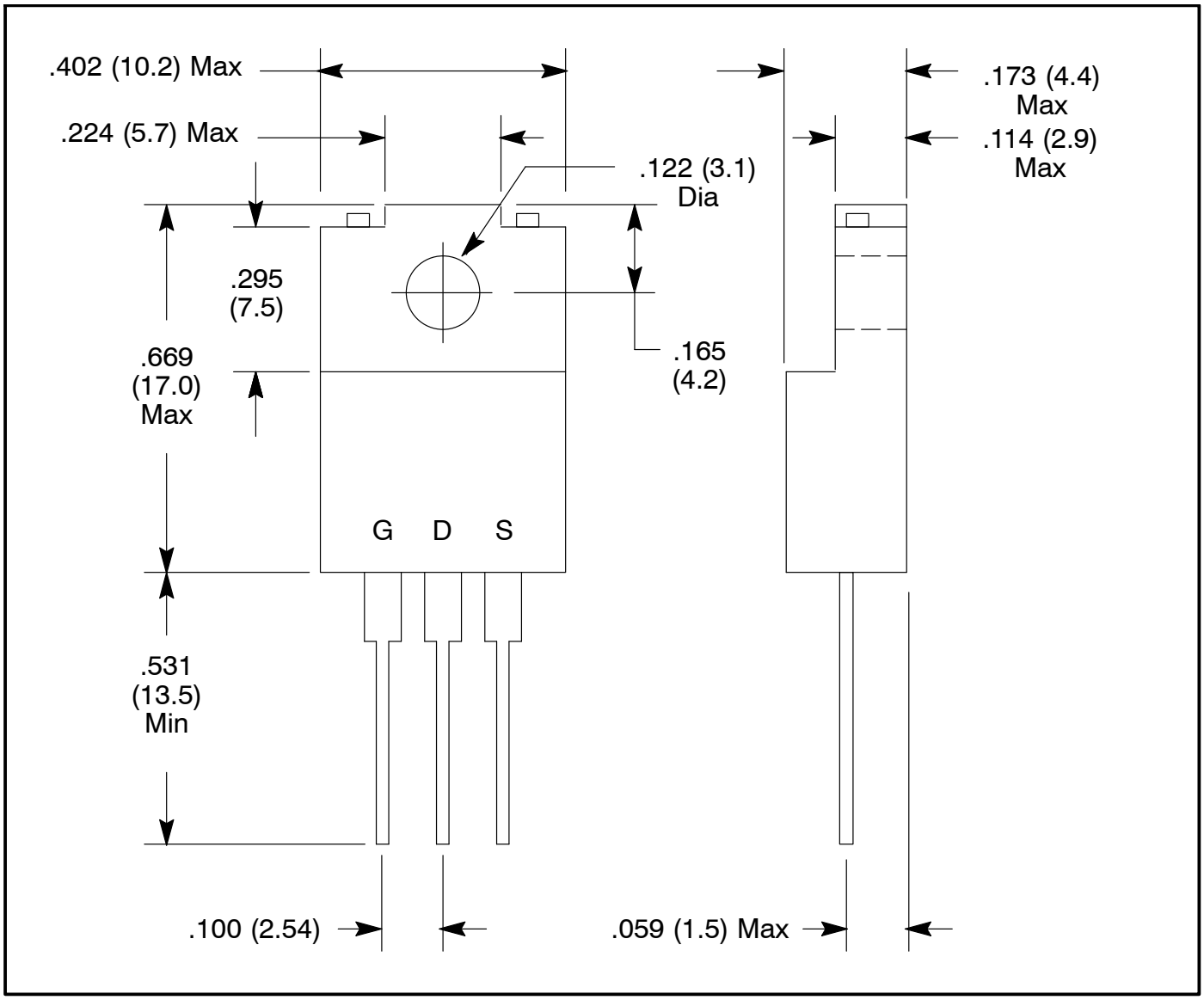
Absolute Maximum Ratings: (T_C = +25°C unless otherwise specified)

Drain–Source Voltage, V_{DSS} 700V
Gate–Source Voltage, V_{GSS} . . . . . ±30V
Drain Current, I_D
  Continuous DC 6A
  Peak (Pulse Width ≤ 10≤s, Duty Cycle ≤ 1/100) 18A
Continuous DC Source Current, I_S 6A
Total Power Dissipation, P_T 50W
Repetitive Avalanche Current (T_{ch} = +150°C), I_{AR} 6A
Single Avalanche Energy (T_{ch} = +25°C), E_{AS} 190mJ
Repetitive Avalanche Energy (T_{ch} = +25°C), E_{AR} 19mJ
Operating Channel Temperature, T_{ch} . . . . . +150°C
Storage Temperature Range, T_{stg} . . . . . –55° to +150°C
Thermal Resistance, Junction–to–Case, R_{thJC} . . . . . 2.5°C/W
Dielectric Strength (Terminals–to–Case, AC, 1 minute), V_{dis} 2kV
Mounting Torque, TOR
  Maximum . . . . . 0.5N•m
  Recommended . . . . . 0.3N•m

Rev. 10–13

Electrical Characteristics: (T_C = +25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain−Source Breakdown Voltage	$V_{(BR)DSS}$	I_D = 1mA, V_{GS} = 0V	700	–	–	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 700V, V_{GS} = 0V	–	–	250	≤A
Gate−Source Leakage Current	I_{GSS}	V_{GS} = ±30V, V_{DS} = 0V	–	–	±0.1	≤A
Forward Transconductance	g_{fs}	I_D = 3A, V_{DS} = 10V	3	5	–	S
Static Drain−Source On−State Resistance	$R_{DS(on)}$	I_D = 3A, V_{GS} = 10V	–	1.5	2.0	±
Gate Threshold Voltage	V_{TH}	I_D = 1mA, V_{DS} = 10V	2.5	3.0	3.5	V
Source−Drain Diode Forward Voltage	V_{SD}	I_S = 3A, V_{GS} = 0V	–	–	1.5	V
Total Gate Charge	Q_g	V_{DD} = 400V, V_{GS} = 10V, I_D = 6A	–	35	–	nC
Input Capacitance	C_{iss}	V_{DS} = 10V, V_{GS} = 0V, f = 1MHz	–	1250	–	pF
Reverse Transfer Capacitance	C_{rss}		–	250	–	pF
Output Capacitance	C_{oss}		–	530	–	pF
Turn−On Time	t_{on}	I_D = 3A, R_L = 50±, V_{GS} = 10V	–	60	110	ns
Turn−Off Time	t_{off}		–	160	250	ns



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